

**SANYO**

No.2253A

**2SA1478/2SC3788**

PNP/NPN Epitaxial Planar Silicon Transistor

High-Definition CRT Display  
Video Output Applications**Features**

- High breakdown voltage :  $V_{CEO} \geq 200V$
- Small reverse transfer capacitance and excellent high frequency characteristic :  $C_{re} = 1.2pF(NPN), 1.7pF(PNP)$
- Adoption of FBET process

( ): 2SA1478

**Absolute Maximum Ratings at  $T_a = 25^\circ C$** 

Absolute Maximum Ratings at Ta=25°C			unit	
Collector-to-Base Voltage	V <sub>CBO</sub>	(-)200	V	
Collector-to-Emitter Voltage	V <sub>CEO</sub>	(-)200	V	
Emitter-to-Base Voltage	V <sub>EBO</sub>	(-)5	V	
Collector Current	I <sub>C</sub>	(-)100	mA	
Collector Current (Pulse)	I <sub>CP</sub>	(-)200	mA	
Collector Dissipation	P <sub>C</sub>	1.3	W	
		Tc=25°C	5	W
Junction Temperature	T <sub>j</sub>	150	°C	
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C	

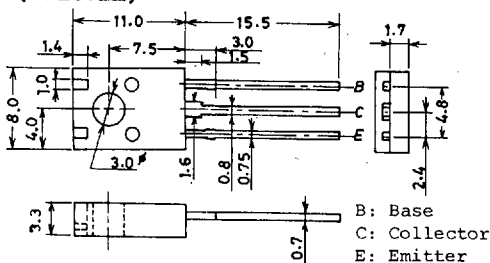
**Electrical Characteristics at  $T_a = 25^\circ C$** 

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = (-)150V, I_E = 0$			(-)0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = (-)10V, I_C = (-)10mA$	40*		320*	
Gain-Bandwidth Product	$f_T$	$V_{CE} = (-)30V, I_C = (-)10mA$		150		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = (-)30V, f = 1MHz$		1.7		pF
				(2.6)		
Reverse Transfer Capacitance	$C_{re}$	$V_{CB} = (-)30V, f = 1MHz$		1.2		pF
				(1.7)		
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)1.0	V

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\*: The 2SA1478/2SC3788 are classified by 10mA  $h_{FE}$  as follows:

40	C	80	60	D	120	100	E	200	160	F	320
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**Package Dimensions 2042A**  
(unit:mm)

SANYO: TO126ML

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			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-) 10 \mu A, I_E = 0$	(-)	200		V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-) 1 mA, R_{BE} = \infty$	(-)	200		V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-) 10 \mu A, I_C = 0$	(-)	5		V

